TL750M, TL751M SERIES LOW-DROPOUT VOLTAGE REGULATORS

SLVS021H - JANUARY 1988 - REVISED JANUARY 2000

- Very Low Dropout Voltage, Less Than 0.6 V at 750 mA
- Low Quiescent Current
- TTL- and CMOS-Compatible Enable on **TL751M Series**
- 60-V Load-Dump Protection
- Overvoltage Protection
- **Internal Thermal Overload Protection**
- Internal Overcurrent-Limiting Circuitry

description

The TL750M and TL751M series are low-dropout positive voltage regulators specifically designed for battery-powered systems. The TL750M and TL751M series incorporate onboard overvoltage and current-limiting protection circuitry to protect the devices and the regulated system. Both series are fully protected against 60-V load-dump and reverse-battery conditions. Extremely low quiescent current, even during full-load conditions, makes the TL750M and TL751M series ideal for standby power systems.

The TL750M and TL751M series offers 5-V, 8-V, 10-V, and 12-V options. The TL751M series has the addition of an enable (ENABLE) input. The ENABLE input gives the designer complete control over power up, allowing sequential power up or emergency shutdown. When ENABLE is high, the regulator output is placed in the high-impedance state. The ENABLE input is TTL- and CMOS-compatible.

The TL750MxxC and TL751MxxC are characterized for operation over the virtual junction temperature range 0°C to 125°C.

AVAILABLE OPTIONS

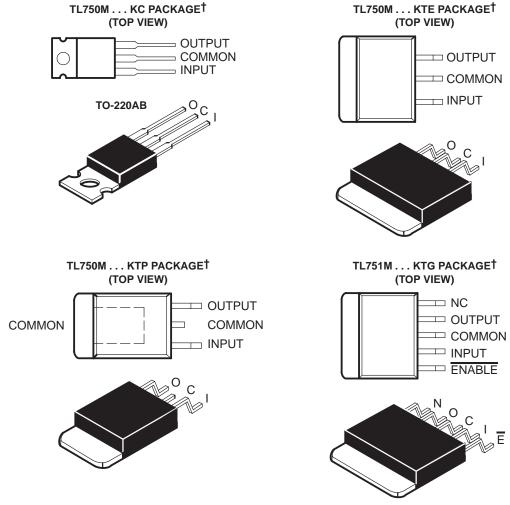
			PACKAGE	D DEVICES		
TJ	V _O TYP (V)	HEAT-SINK MOUNTED (3-PIN) (KC)	PLASTIC FLANGE MOUNT (KTE)	PLASTIC FLANGE MOUNT (KTG)	PLASTIC FLANGE MOUNT (KTP)	CHIP FORM (Y)
	5	TL750M05CKC	TL750M05CKTE	TL751M05CKTG	TL750M05CKTPR	TL750M05Y
0°C to 125°C	8	TL750M08CKC	TL750M08CKTE	TL751M08CKTG	TL750M08CKTPR	TL750M08Y
0.0 10 125.0	10	TL750M10CKC	TL750M10CKTE	TL751M10CKTG	TL750M10CKTPR	TL750M10Y
	12	TL750M12CKC	TL750M12CKTE	TL751M12CKTG	TL750M12CKTPR	TL750M12Y

The KTE and KTG packages are available taped and reeled. The KTP is only available taped and reeled. Add the suffix R to device type (e.g., TL750M05CKTER). Chip forms are tested at 25°C.



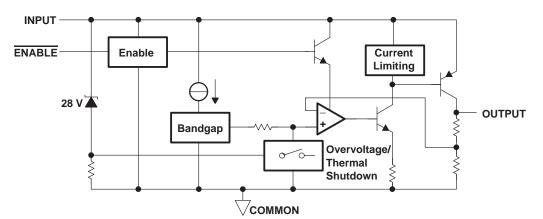
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





 $[\]ensuremath{^{\dagger}}$ The common terminal is in electrical contact with the mounting base. NC – No internal connection

TL751Mxx functional block diagram



DEVICE COMPONENT COUNT				
Transistors	46			
Diodes	14			
Resistors	44			
Capacitors	4			
JFETs	1			
Tunnels (emitter R)	2			

absolute maximum ratings over virtual junction temperature range (unless otherwise noted)†

Continuous input voltage		26 V
Transient input voltage (see Figure 3)		60 V
Continuous reverse input voltage		
Transient reverse input voltage: t = 100 ms		
Package thermal impedance, θ_{JA} (see Notes 1 and 2):	KC package .	22°C/W
	KTE package	23°C/W
	KTG package	23°C/W
	KTP package	28°C/W
Virtual junction temperature range, T _J		0°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10	seconds	260°C
Storage temperature range, T _{stq}		–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is P_D = (T_J(max) T_A)/θ_{JA}. Operating at the absolute maximum T_J of 150°C can impact reliability. Due to variation in individual device electrical characteristics and thermal resistance, the built-in thermal overload protection may be activated at power levels slightly above or below the rated dissipation.
 - 2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

		MIN	MAX	UNIT
	TL75xM05	6	26	
Input voltage range, V _I	TL75xM08	9	26	V
	TL75xM10	11	26	V
	TL75xM12	13	26	
High-level ENABLE input voltage, VIH	TL751Mxx	2	15	V
Low-level ENABLE input voltage, V _{IL}	TL751Mxx	0	0.8	V
Output current range, IO	TL75xMxxC		750	mA
Operating virtual junction temperature range, TJ	TL75xMxxC	0	125	°C

electrical characteristics, V_I = 14 V, I_O = 300 mA, T_J = 25°C

PARAMETER	TL	LINIT		
PARAMETER	MIN TYP MAX	UNIT		
Response time, ENABLE to output		50		μs



electrical characteristics, V_I = 14 V, I_O = 300 mA, \overline{ENABLE} at 0 V for TL751M05, T_J = 25°C (unless otherwise noted) (see Note 3)

PARAMETER	TEST CONDITIONS		TL TL	UNIT		
			MIN	TYP	MAX	
Output voltage			4.95	5	5.05	V
	$T_J = 0^{\circ}C$ to $125^{\circ}C$		4.9		5.1	٧
Input voltage regulation	$V_{I} = 9 V \text{ to } 16 V,$	$I_O = 250 \text{ mA}$		10	25	mV
Input voltage regulation	$V_{I} = 6 V \text{ to } 26 V,$	$I_O = 250 \text{ mA}$		12	50	mv
Ripple rejection	$V_{I} = 8 V \text{ to } 18 V,$	f = 120 Hz	50	55		dB
Output voltage regulation	$I_{O} = 5 \text{ mA to } 750 \text{ mA}$			20	50	mV
Dropout voltage	I _O = 500 mA				0.5	V
Dropout voltage	$I_{O} = 750 \text{ mA}$				0.6	V
Output noise voltage	f = 10 Hz to 100 kHz			500		μV
Bias current	I _O = 750 mA I _O = 10 mA			60	75	mA
bias current					5	IIIA
Bias current (TL751M05C and TL751M05Q only)	ENABLE V _{IH} ≥ 2 V				200	μΑ

NOTE 3: Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-µF capacitor across the input and a 10-µF tantalum capacitor on the output, with equivalent series resistance within the guidelines shown in Figure 3.

electrical characteristics, V_I = 14 V, I_O = 300 mA, \overline{ENABLE} at 0 V for TL751M08, T_J = 25°C (unless otherwise noted) (see Note 3)

PARAMETER	TEST CONDITIONS	TL750M08C TL751M08C			UNIT
		MIN	TYP	MAX 8.08 8.16 40 68 80 0.5 0.6	
Output voltage		7.92	8	8.08	V
Output voltage	$T_J = 0$ °C to 125°C	7.84		8.16	V
Input voltage regulation	$V_{I} = 10 \text{ V to } 17 \text{ V}, \qquad I_{O} = 250 \text{ mA}$		12	40	mV
Imput voltage regulation	$V_{I} = 9 \text{ V to } 26 \text{ V}, \qquad I_{O} = 250 \text{ mA}$		15	68	IIIV
Ripple rejection	V _I = 11 V to 21 V, f = 120 Hz	50	55		dB
Output voltage regulation	I _O = 5 mA to 750 mA		24	80	mV
Dropout voltage	I _O = 500 mA			0.5	V
Diopout voitage	I _O = 750 mA	7.92 8 8.08 7.84 8.16 12 40 15 68 50 55 24 80 0.5 0.6 500 60 75	V		
Output noise voltage	f = 10 Hz to 100 kHz		500		μV
Bias current	I _O = 750 mA		60	75	mΛ
Dids current	I _O = 10 mA			5	mA
Bias current (TL751Mxx only)	ENABLE V _{IH} ≥ 2 V			200	μΑ

NOTE 3: Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-µF capacitor across the input and a 10-µF tantalum capacitor on the output, with equivalent series resistance within the guidelines shown in Figure 3.



electrical characteristics, V_I = 14 V, I_O = 300 mA, \overline{ENABLE} at 0 V for TL751M10, T_J = 25°C (unless otherwise noted) (see Note 3)

PARAMETER	TEST CONDITIONS	TL750M10C TL751M10C			UNIT	
		MIN	TYP	_		
Output voltage		9.9	10	10.1	V	
Output voltage	$T_J = 0$ °C to 125°C	9.8		10.2	V	
Input voltage regulation	$V_{I} = 12 \text{ V to } 18 \text{ V}, \qquad I_{O} = 250 \text{ mA}$		15	43	mV	
Imput voltage regulation	$V_{I} = 11 \text{ V to } 26 \text{ V}, \qquad I_{O} = 250 \text{ mA}$		20	75	1117	
Ripple rejection	$V_{I} = 13 \text{ V to } 23 \text{ V}, \qquad \qquad f = 120 \text{ Hz}$	50	55		dB	
Output voltage regulation	$I_O = 5 \text{ mA to } 750 \text{ mA}$		30	100	mV	
Dropout voltage	I _O = 500 mA			0.5	V	
Dropout voltage	I _O = 750 mA			0.6	V	
Output noise voltage	f = 10 Hz to 100 kHz		1000		μV	
Diag current	I _O = 750 mA		60	75	A	
Bias current	I _O = 10 mA			5	mA	
Bias current (TL751Mxx only)	ENABLE V _{IH} ≥ 2 V			200	μΑ	

NOTE 3: Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-μF capacitor across the input and a 10-μF tantalum capacitor on the output, with equivalent series resistance within the guidelines shown in Figure 3.

electrical characteristics, V_I = 14 V, I_O = 300 mA, \overline{ENABLE} at 0 V for TL751M12, T_J = 25°C (unless otherwise noted) (see Note 3)

PARAMETER	TEST CO	TEST CONDITIONS		TL750M12C TL751M12C		
			MIN	TLT51M12C MIN TYP MAX 11.88 12 12.12 11.76 15 43 20 78 50 55 30 120 0.5 0.6 1000 75]	
Output valtage			11.88	12	12.12	V
Output voltage	$T_J = 0$ °C to 125°C		11.76		12.24	v
lanut voltage regulation	V _I = 14 V to 19 V,	I _O = 250 mA		15	43	mV
Input voltage regulation	V _I = 13 V to 26 V,	I _O = 250 mA		20	78	mv
Ripple rejection	V _I = 13 V to 23 V,	f = 120 Hz	50	55		dB
Output voltage regulation	$I_O = 5 \text{ mA to } 750 \text{ mA}$			30	120	mV
Dronout voltage	I _O = 500 mA	I _O = 500 mA			0.5	V
Dropout voltage	I _O = 750 mA		50 55 30 120 0.5	V		
Output noise voltage	f = 10 Hz to 100 kHz			1000		μV
Dies surrent	I _O = 750 mA	I _O = 750 mA I _O = 10 mA		60	75	A
Bias current	I _O = 10 mA				5	mA
Bias current (TL751Mxx only)	ENABLE V _{IH} ≥ 2 V				200	μΑ

NOTE 3: Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-μF capacitor across the input and a 10-μF tantalum capacitor on the output, with equivalent series resistance within the guidelines shown in Figure 3.

electrical characteristics, $V_I = 14 \text{ V}$, $I_O = 300 \text{ mA}$, $\overline{\text{ENABLE}}$ at 0 V, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted) (see Note 3)

PARAMETER	TEST CONDITIONS			TL750M05Y			
PARAMETER	1231 00	CNOTTIONS	MIN	TYP	MAX	UNIT	
Output voltage				5		V	
Input voltage regulation	V _I = 9 V to 16 V,	$I_{O} = 250 \text{ mA}$		10		mV	
Input voltage regulation	$V_{I} = 6 \text{ V to } 26 \text{ V},$	$I_O = 250 \text{ mA}$		12		IIIV	
Ripple rejection	V _I = 8 V to 18 V,	f = 120 Hz		55		dB	
Output voltage regulation	I _O = 5 mA to 750 mA			20		mV	
Output noise voltage	f = 10 Hz to 100 kHz			500		μV	
Bias current	I _O = 750 mA			60		mA	

NOTE 3: Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-μF capacitor across the input and a 10-μF tantalum capacitor on the output, with equivalent series resistance within the guidelines shown in Figure 3.

electrical characteristics, V_I = 14 V, I_O = 300 mA, ENABLE at 0 V, T_J = 25°C (unless otherwise noted) (see Note 3)

PARAMETER	TEST CO	TL	UNIT			
PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
Output voltage				8		V
Input voltage regulation	V _I = 10 V to 17 V,	I _O = 250 mA		12		mV
Imput voltage regulation	$V_{I} = 9 V \text{ to } 26 V,$	$I_0 = 250 \text{ mA}$		15		IIIV
Ripple rejection	V _I = 11 V to 21 V,	f = 120 Hz		55		dB
Output voltage regulation	I _O = 5 mA to 750 mA			24		mV
Output noise voltage	f = 10 Hz to 100 kHz			500		μV
Bias current	I _O = 750 mA	·		60		mA

NOTE 3: Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-μF capacitor across the input and a 10-μF tantalum capacitor on the output, with equivalent series resistance within the guidelines shown in Figure 3.

electrical characteristics, $V_I = 14 \text{ V}$, $I_O = 300 \text{ mA}$, $\overline{\text{ENABLE}}$ at 0 V, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted) (see Note 3)

PARAMETER	TEST CO	TL	TL750M10Y				
PARAMETER	1231 00	MULLIONS	MIN	TYP	MAX	UNIT	
Output voltage				10		V	
Input voltage regulation	V _I = 12 V to 18 V,	I _O = 250 mA		15		mV	
Input voltage regulation	$V_I = 11 \text{ V to } 26 \text{ V},$	$I_0 = 250 \text{ mA}$		20		IIIV	
Ripple rejection	$V_I = 13 \text{ V to } 23 \text{ V},$	f = 120 Hz		55		dB	
Output voltage regulation	$I_O = 5 \text{ mA to } 750 \text{ mA}$			30		mV	
Output noise voltage	f = 10 Hz to 100 kHz			1000		μV	
Bias current	I _O = 750 mA			60		mA	

NOTE 3: Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-μF capacitor across the input and a 10-μF tantalum capacitor on the output, with equivalent series resistance within the guidelines shown in Figure 3.



TL751M12Y electrical characteristics, $V_I = 14 \text{ V}$, $I_O = 300 \text{ mA}$, $\overline{\text{ENABLE}}$ at 0 V, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted) (see Note 3)

DADAMETED	PARAMETER TEST CONDITIONS		TL750M12Y			UNIT	
PARAMETER			MIN	TYP	MAX	UNIT	
Output voltage				12		V	
Input voltage regulation	V _I = 14 V to 19 V,	I _O = 250 mA		15		m∨	
Input voltage regulation	$V_I = 13 \text{ V to } 26 \text{ V},$	$I_O = 250 \text{ mA}$		20			
Ripple rejection	$V_I = 13 \text{ V to } 23 \text{ V},$	f = 120 Hz		55		dB	
Output voltage regulation	I _O = 5 mA to 750 mA			30		mV	
Output noise voltage	f = 10 Hz to 100 kHz			1000		μV	
Bias current	I _O = 750 mA			60		mA	

NOTE 3: Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-μF capacitor across the input and a 10-μF tantalum capacitor on the output, with equivalent series resistance within the guidelines shown in Figure 3.

PARAMETER MEASUREMENT INFORMATION

The TL751Mxx is a low-dropout regulator. This means that the capacitance loading is important to the performance of the regulator because it is a vital part of the control loop. The capacitor value and the equivalent series resistance (ESR) both affect the control loop and must be defined for the load range and the temperature range. Figures 1 and 2 can establish the capacitance value and ESR range for the best regulator performance.

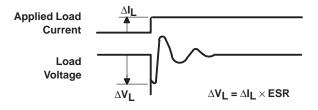
Figure 1 shows the recommended range of ESR for a given load with a 10- μ F capacitor on the output. This figure also shows a maximum ESR limit of 2 Ω and a load-dependent minimum ESR limit.

For applications with varying loads, the lightest load condition should be chosen because it is the worst case. Figure 2 shows the relationship of the reciprocal of ESR to the square root of the capacitance with a minimum capacitance limit of 10 μF and a maximum ESR limit of 2 Ω . This figure establishes the amount that the minimum ESR limit shown in Figure 1 can be adjusted for different capacitor values. For example, where the minimum load needed is 200 mA, Figure 2 suggests an ESR range of 0.8 Ω to 2 Ω for 10 μF . Figure 2 shows that changing the capacitor from 10 μF to 400 μF can change the ESR minimum by greater than 3/0.5 (or 6). Therefore, the new minimum ESR value is 0.8/6 (or 0.13 Ω). This allows an ESR range of 0.13 Ω to 2 Ω , achieving an expanded ESR range by using a larger capacitor at the output. For better stability in low-current applications, a small resistance placed in series with the capacitor (see Table 1) is recommended, so that ESRs better approximate those shown in Figures 1 and 2.

PARAMETER MEASUREMENT INFORMATION

Table 1. Compensation for Increased Stability at Low Currents

MANUFACTURER	CAPACITANCE	ESR TYP	PART NUMBER	ADDITIONAL RESISTANCE
AVX	15 μF	0.9 Ω	TAJB156M010S	1 Ω
KEMET	33 μF	0.6 Ω	T491D336M010AS	0.5 Ω



OUTPUT CAPACITOR EQUIVALENT SERIES RESISTANCE (ESR)

LOAD CURRENT RANGE

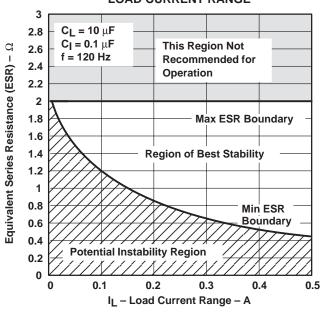


Figure 1

STABILITY vs EQUIVALENT SERIES RESISTANCE (ESR)

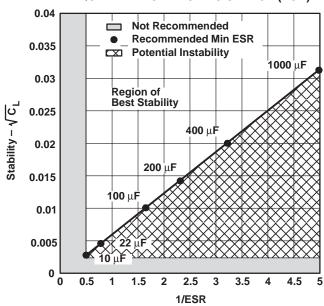


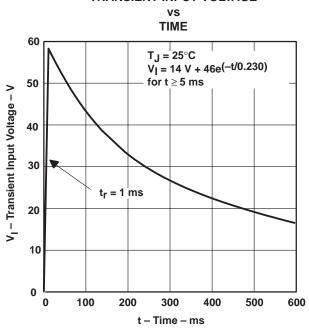
Figure 2

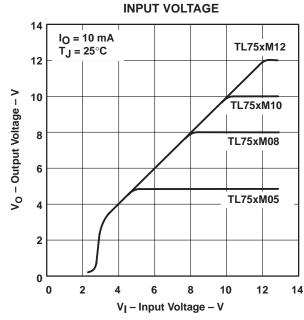
TYPICAL CHARACTERISTICS

Table of Graphs

	FIGURE	
Transient input voltage vs Time	3	
Output voltage vs Input voltage	4	
Input current vs Input voltage	I _O = 10 mA	5
	I _O = 100 mA	6
Dropout voltage vs Output current	7	
Quiescent current vs Output curren	8	
Load transient response	9	
Line transient response	10	

TRANSIENT INPUT VOLTAGE

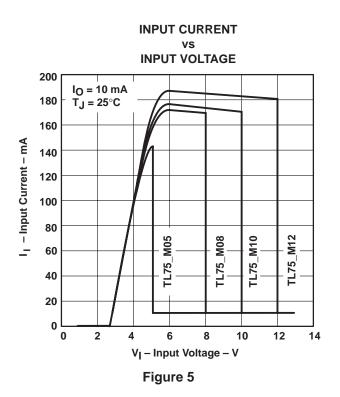


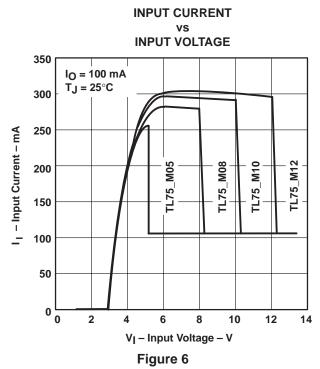


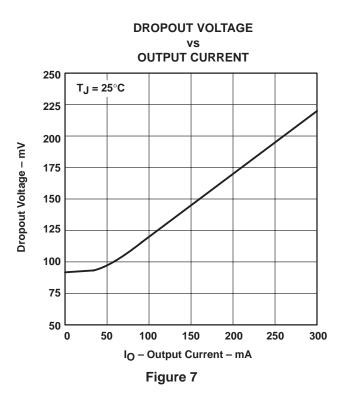
OUTPUT VOLTAGE

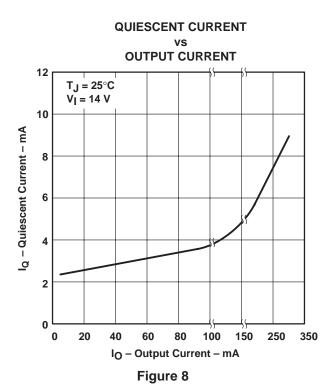
Figure 3 Figure 4

TYPICAL CHARACTERISTICS

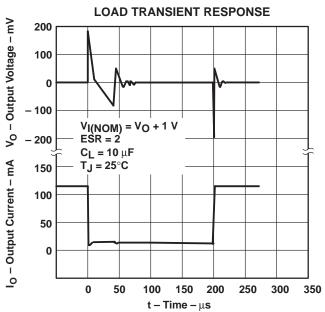








TYPICAL CHARACTERISTICS



t – Time – μs
Figure 9

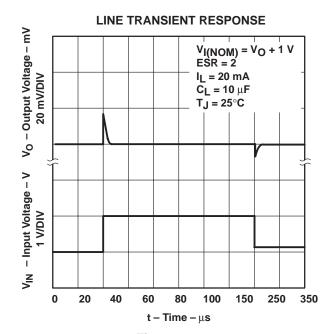


Figure 10

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